

Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant

Parameter	Rating	Units
V_{DS}	1200	V
$I_D @ 25^\circ\text{C}$	64	A
$R_{DS(on)}$	32	m Ω



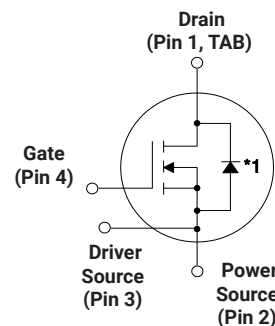
Applications

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating



Inner circuit

TO-247-4
Package



- (1) Drain
- (2) Power Source
- (3) Driver Source
- (4) Gate

*1 Body Diode

Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1200	V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
V_{GSmax}	Gate - Source Voltage (dynamic)	-8/+19	V	AC ($f > 1\text{ Hz}$)	
V_{GSop}	Gate - Source Voltage (static)	-4/+15	V	Static	
I_D	Continuous Drain Current	64	A	$V_{GS} = 15\text{ V}, T_C = 25^\circ\text{C}$	
		50		$V_{GS} = 15\text{ V}, T_C = 100^\circ\text{C}$	
$I_{D(pulse)}$	Pulsed Drain Current	120	A	Pulse width t_p limited by T_{jmax}	
P_D	Power Dissipation	288	W	$T_C = 25^\circ\text{C}, T_J = 175^\circ\text{C}$	
T_J, T_{stg}	Operating Junction and Storage Temperature	-40 to +175	$^\circ\text{C}$		
T_L	Solder Temperature	260	$^\circ\text{C}$	1.6mm (0.063") from case for 10s	

Note (1): When using MOSFET Body Diode $V_{GSmax} = -4\text{V}/+19\text{V}$

Note (2): MOSFET can also safely operate at $0/+15\text{ V}$



Electrical Characteristics (T_c = 25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
V _{(BR)DSS}	Drain-Source Breakdown Voltage	1200			V	V _{GS} = 0 V, I _D = 100 μA	
V _{GS(th)}	Gate Threshold Voltage	1.8	2.5	3.6	V	V _{DS} = V _{GS} , I _D = 11.5 mA	
			2.0		V	V _{DS} = V _{GS} , I _D = 11.5 mA, T _J = 175°C	
I _{DSS}	Zero Gate Voltage Drain Current		1	50	μA	V _{DS} = 1200 V, V _{GS} = 0 V	
I _{GSS}	Gate-Source Leakage Current		10	250	nA	V _{GS} = 15 V, V _{DS} = 0 V	
R _{DS(on)}	Drain-Source On-State Resistance	23	32	45	mΩ	V _{GS} = 15 V, I _D = 40 A	
			56			V _{GS} = 15 V, I _D = 40 A, T _J = 175°C	
g _{fs}	Transconductance		27		S	V _{DS} = 20 V, I _{DS} = 40 A	
			22			V _{DS} = 20 V, I _{DS} = 40 A, T _J = 175°C	
C _{iss}	Input Capacitance		3180		pF	V _{GS} = 0 V, V _{DS} = 800 V f = 100 kHz V _{AC} = 25 mV	
C _{oss}	Output Capacitance		129				
C _{rss}	Reverse Transfer Capacitance		8				
E _{oss}	C _{oss} Stored Energy		76				
E _{ON}	Turn-On Switching Energy (SiC Diode FWD)		366		μJ	V _{DS} = 800 V, V _{GS} = -4 V/+15 V, I _D = 40 A, R _{G(ext)} = 2.5 Ω, L = 65.7 μH, T _J = 175°C	
E _{OFF}	Turn Off Switching Energy (SiC Diode FWD)		123				
E _{ON}	Turn-On Switching Energy (Body Diode FWD)		955		μJ	V _{DS} = 800 V, V _{GS} = -4 V/+15 V, I _D = 40 A, R _{G(ext)} = 2.5 Ω, L = 65.7 μH, T _J = 175°C	
E _{OFF}	Turn Off Switching Energy (Body Diode FWD)		107				
t _{d(on)}	Turn-On Delay Time		27		ns	V _{DD} = 800 V, V _{GS} = -4 V/15 V R _{G(ext)} = 2.5 Ω, I _D = 40 A, L = 65.7 Timing relative to V _{DS} , Inductive load	
t _r	Rise Time		18				
t _{d(off)}	Turn-Off Delay Time		32				
t _f	Fall Time		9				
R _{G(int)}	Internal Gate Resistance		1.7		Ω	f = 1 MHz, V _{AC} = 25 mV	
Q _{gs}	Gate to Source Charge		40		nC	V _{DS} = 800 V, V _{GS} = -4 V/15 V I _D = 40 A Per IEC60747-8-4 pg 21	
Q _{gd}	Gate to Drain Charge		34				
Q _g	Total Gate Charge		116				



Reverse Diode Characteristics (T_c = 25°C unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V _{SD}	Diode Forward Voltage	4.6		V	V _{GS} = -4 V, I _{SD} = 20 A, T _J = 25 °C	
		4.2		V	V _{GS} = -4 V, I _{SD} = 20 A, T _J = 175 °C	
I _S	Continuous Diode Forward Current		62	A	V _{GS} = -4 V, T _C = 25 °C	
I _{S, pulse}	Diode pulse Current		120	A	V _{GS} = -4 V, pulse width t _p limited by T _{jmax}	
t _{rr}	Reverse Recover time	27		ns	V _{GS} = -4 V, I _{SD} = 40 A, V _R = 800 V dif/dt = 2250 A/μs, T _J = 175 °C	
Q _{rr}	Reverse Recovery Charge	478		nC		
I _{rrm}	Peak Reverse Recovery Current	27		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
R _{θJC}	Thermal Resistance from Junction to Case	0.45	°C/W		
R _{θJA}	Thermal Resistance From Junction to Ambient	40			

Package Dimensions

Unit: mm

